KST5N10Z

100V N-Channel MOSFET

General Description

The KST5N10Z uses advanced MOSFET technology to provide excellent R_{DS}(ON), low gate charge fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable to use in

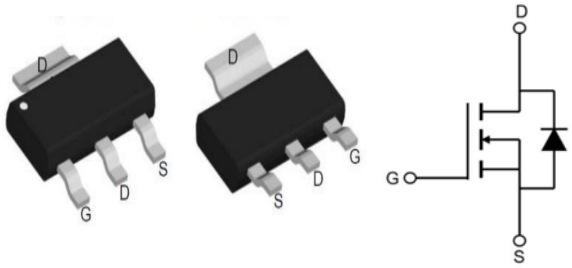
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)
100	166 at V_{GS} = 10 V	5
	190 atV_{GS} = 4.5 V	3.2

Features

- High density cell design for ultra low R_{DS}(on)
- Green Device Available
- Excellent package for good heat dissipation

SOT-223 Pin Configuration



Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!
100% ΔVds TESTED!

Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	5.0	A
	Drain Current – Continuous (T_C=100℃)	3.2	A
I_{DM}	Drain Current – Pulsed[1]	21	A
P_D	Power Dissipation (T_C=25℃)	4	W
	Power Dissipation – Derate above 25℃	0.5	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	58	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	12.4	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.01	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=100V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=5A	---	166	198	mΩ
		V_{GS}=4.5V , I_D=3A	---	190	230	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.78	2.4	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	1.6	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_S=5A	---	10	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=50V , V_{GS}=10V , I_D=5A	---	10	17	nC
Q_{gs}	Gate-Source Charge[2,3]		---	2.1	4.0	
Q_{gd}	Gate-Drain Charge[2,3]		---	3.0	4.1	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=30V , V_{GS}=10V , R_G=3.0 Ω I_D=2A	---	8.5	13	ns
T_r	Rise Time[2,3]		---	6.4	8	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	25.6	34	
T_f	Fall Time[2,3]		---	6.2	8.3	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , F=1MHz	---	780	956	pF
C_{oss}	Output Capacitance		---	113	156	
C_{rss}	Reverse Transfer Capacitance		---	65	86	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	5	A
I_{SM}	Pulsed Source Current		---	---	13	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

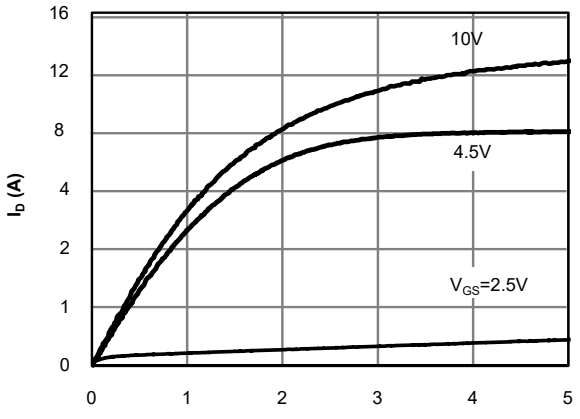


Figure 1: On-Region Characteristics

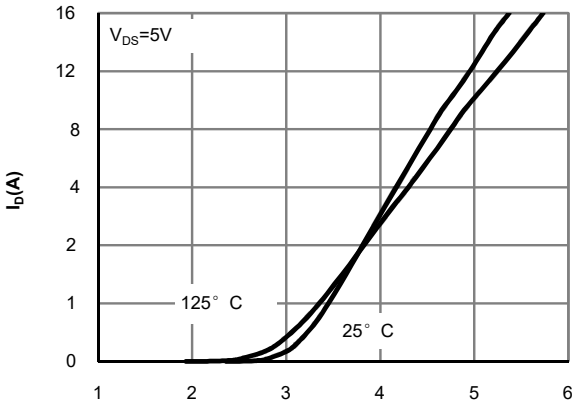


Figure 2: Transfer Characteristics

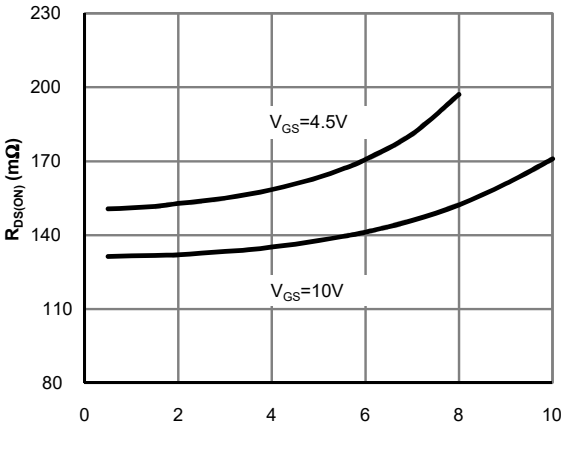


Figure3:On-Resistancevs.DrainCurrentandGateVoltage

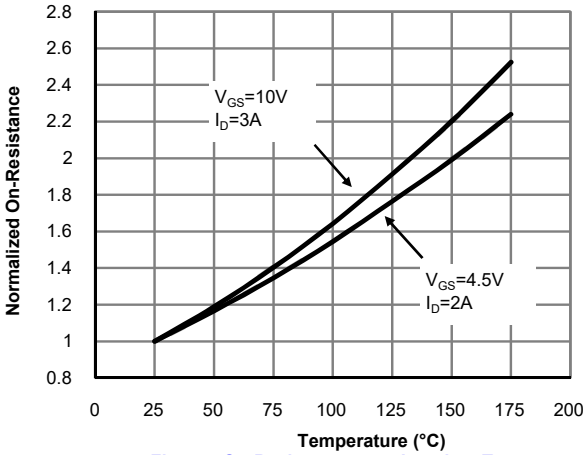


Figure4:On-Resistance vs. Junction Temperature

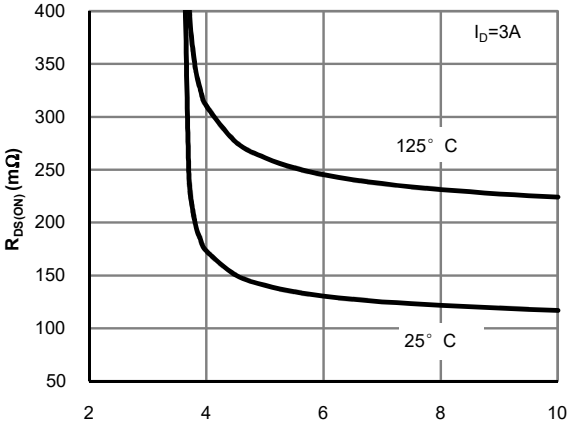


Figure 5: On-Resistance vs. Gate-Source Voltage

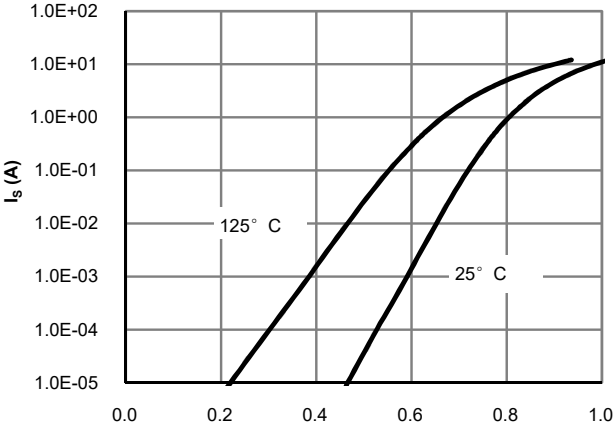


Figure 6: Body-Diode Characteristics

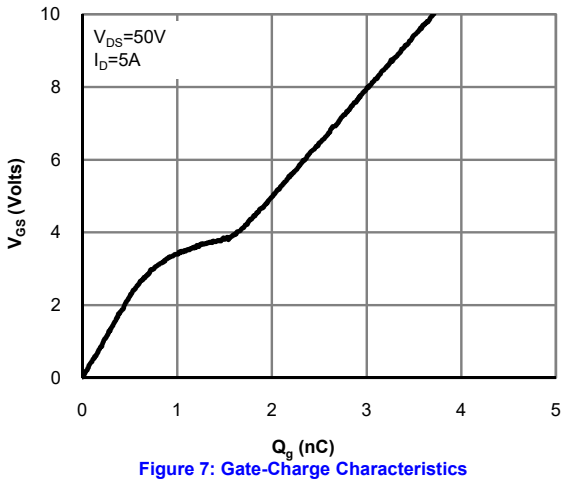


Figure 7: Gate-Charge Characteristics

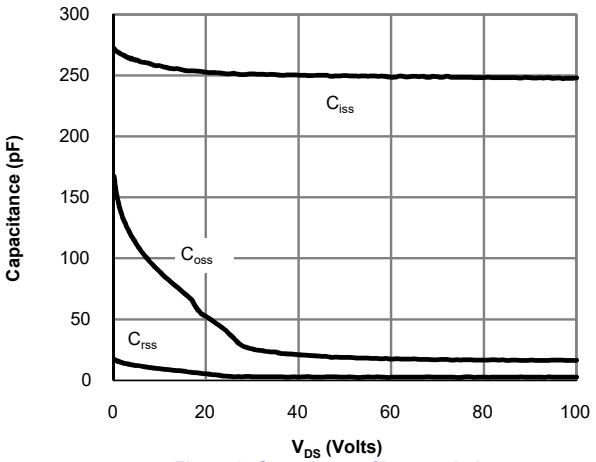


Figure 8: Capacitance Characteristics

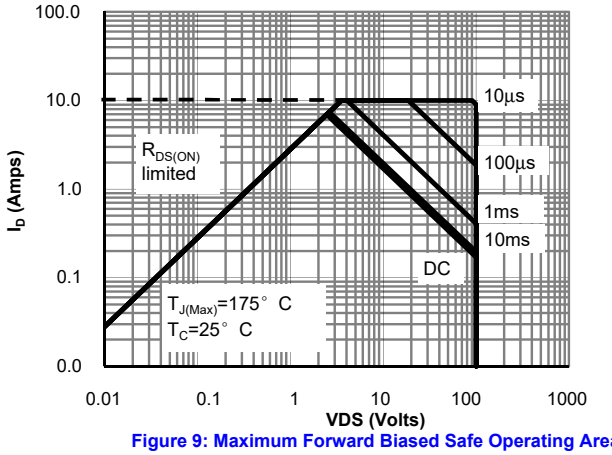


Figure 9: Maximum Forward Biased Safe Operating Area

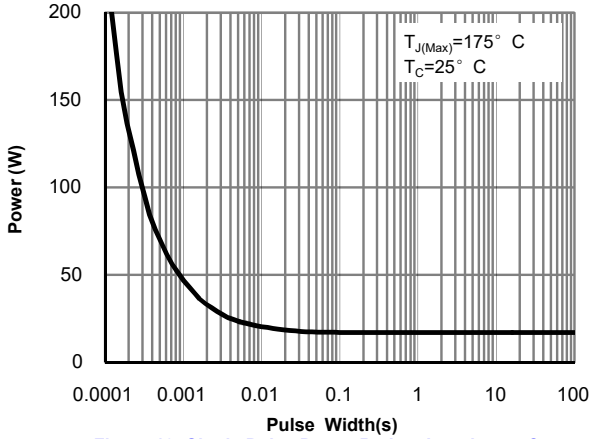


Figure 10: Single Pulse Power Rating Junction-to-Case

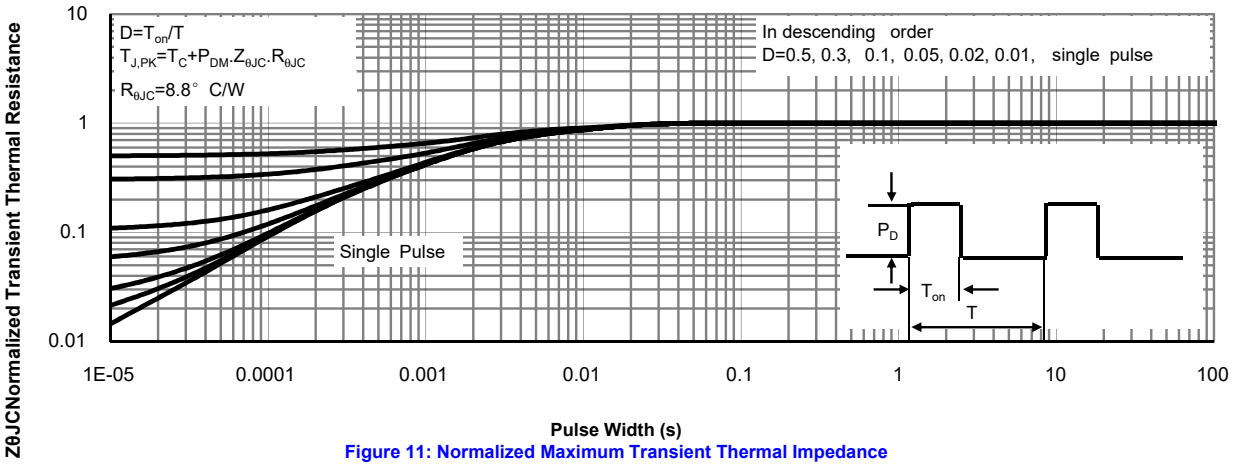


Figure 11: Normalized Maximum Transient Thermal Impedance

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